

SOT-523 Plastic-Encapsulated Diodes

BAS16T/BAW56T/BAV70T/BAV99T

SWITCHING DIODE

FEATURES

Power dissipation

$$P_D: 150 \text{ mW (} T_{amb}=25^\circ\text{C)}$$

Forward Current

$$I_F: 75 \text{ mA}$$

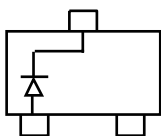
Reverse Voltage

$$V_R: 85 \text{ V}$$

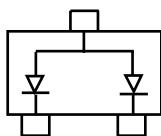
Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$

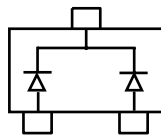
SOT-523



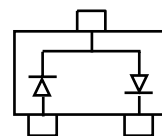
BAS16T Marking: A2



BAW56T Marking: JD



BAV70T Marking: JJ



BAV99T Marking: JE

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	85		V
Reverse voltage leakage current	I_{R1}	$V_R=75\text{V}$		2	μA
	I_{R2}	$V_R=25\text{V}$		0.03	μA
Forward voltage	V_F	$I_F=1\text{mA}$ $I_F=10\text{mA}$ $I_F=50\text{mA}$ $I_F=150\text{mA}$		715 855 1000 1250	mV
Diode capacitance	C_D	$V_R=0\text{V}, f=1\text{MHz}$		1.5	pF
Reverse recovery time	t_{rr}			4	nS

Typical Characteristics

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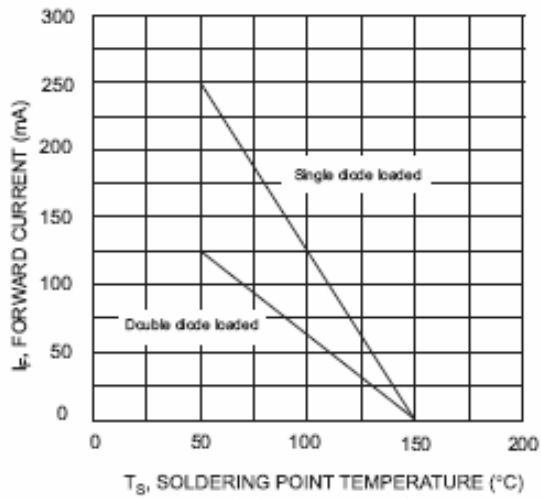


Fig. 1 Current Derating Curve

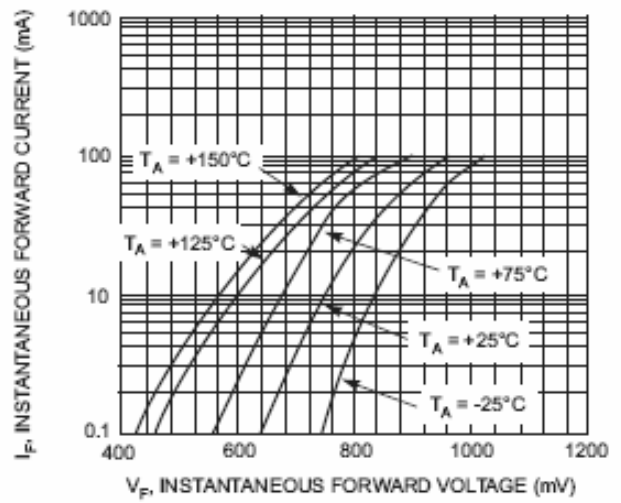


Fig. 2, Typical Forward Characteristics

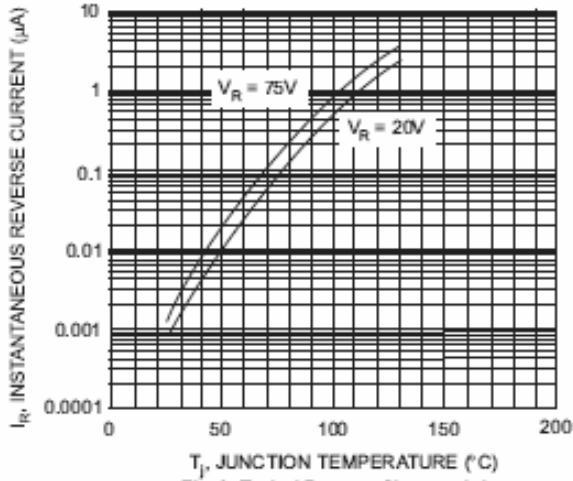


Fig. 3, Typical Reverse Characteristics